

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **General Description**

The MAX14611 is a quad bidirectional logic-level translator that provides the level shifting necessary to allow data transfer in a multivoltage system. Externally applied voltages, V<sub>CC</sub> and V<sub>I</sub>, set the logic levels on either side of the device. A low-voltage logic signal present on the V<sub>I</sub> side of the device appears as a high-voltage logic signal on the V<sub>CC</sub> side of the device, and vice-versa.

The device is ideal for I2C bus as well as MDIO bus applications where open-drain operation is often required. The device features a three-state output mode (TS). Drive TS high to connect the pullup to the powered I/O port. This allows for continuous, undisrupted I2C operation on the powered side of the device while the level translation function is off. The MAX14611 is a pin-to-pin compatible upgrade to the MAX3378E in the TDFN package.

The MAX14611 features enhanced high-electrostaticdischarge (ESD) protection on all I/OVCC\_ ports up to ±6kV HBM. The device operates over the -40°C to +85°C extended temperature range and is available in 3mm x 3mm, 14-pin TDFN and 4.9mm x 5.1mm, 14-pin TSSOP packages.

#### **Applications**

SPI, I2C, and MDIO Level Translation Low-Voltage ASIC Level Translation Portable Electronics

Mobile Phones **POS Systems** Telecommunications Equipment

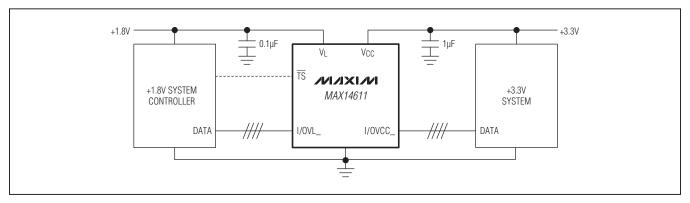
### **Benefits and Features**

- **♦** Improved Interoperability
  - ♦ Meets I<sup>2</sup>C Specifications
  - ♦ 10kΩ Internal Pullup Resistor
  - ♦ Pin-to-Pin Compatible with the MAX3377E and the MAX3378E
  - ♦ 0.9V Operation on Low Voltage Supply
- **♦** Robust Logic-Level Translation

  - I/OVCC Lines
  - ♦ Thermal Short-Circuit Protection
  - ♦ Short to Ground Fault Protection on All Pins
  - → -40°C to +85°C Operating Temperature Range
- ♦ Increased Design Flexibility
  - ♦ Ultra-Low Supply Current
  - ♦ Pullup Resistor Enabled with a Single Power Supply when  $\overline{TS} = High$
  - ♦ 10Ω (max) Transmission Gate FET
  - ♦ Small, 14-Pin, 3.0mm x 3.0mm TDFN Package and 14-Pin, 4.9mm x 5.1mm TSSOP Package

Ordering Information appears at end of data sheet.

## Typical Operating Circuit



For related parts and recommended products to use with this part, refer to www.maxim-ic.com/MAX14611.related.

MIXIM

Maxim Integrated Products 1

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

#### **ABSOLUTE MAXIMUM RATINGS**

(All voltages referenced to GND.)	Continuous Power Dissipation (T <sub>A</sub> = +70°C)
V <sub>CC</sub> 0.5V to +6V	TDFN (derate 24.4mW/°C above +70°C)1951.2mW
V <sub>L</sub> 0.5V to +5.5V	TSSOP (derate 10mW/°C above +70°C)796.8mW
TS0.5V to +6V	Operating Temperature Range40°C to +85°C
I/OVCC0.5V to (V <sub>CC</sub> + 0.5V)	Maximum Junction Temperature+150°C
I/OVL0.5V to (V <sub>I</sub> + 0.5V)	Storage Temperature Range65°C to +150°C
Short-Circuit Duration I/OVL_, I/OVCC_ to GNDContinuous	Lead Temperature (soldering, 10s)+300°C
Continuous Current±50mA	Soldering Temperature (reflow)+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### PACKAGE THERMAL CHARACTERISTICS (Note 1)

TDFN-EP	TSSOP
Junction-to-Ambient Thermal Resistance (θ <sub>JA</sub> )41°C/W	Junction-to-Ambient Thermal Resistance ( $\theta_{JA}$ )100.4°C/W
Junction-to-Case Thermal Resistance (θ <sub>JC</sub> )8°C/W	Junction-to-Case Thermal Resistance ( $\theta_{JC}$ )30°C/W

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a fourlayer board. For detailed information on package thermal considerations, refer to www.maxim-ic.com/thermal-tutorial.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{CC} = +1.65 \text{V to } +5.5 \text{V}, V_L = 0.9 \text{V to the lesser of } V_{CC} + 0.3 \text{V} \text{ and 5V}. T_A = T_J = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ values are at  $V_{CC} = +3.3V$ ,  $V_L = +1.8V$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLIES						
V <sub>L</sub> Supply Range	VL		0.9		5	V
V <sub>CC</sub> Supply Range	V <sub>CC</sub>		1.65		5.5	V
V <sub>L</sub> Supply Current	I <sub>VL</sub>	$I/OVCC_{-} = V_{CC}, I/OVL_{-} = V_{L}, \overline{TS} = V_{L}$			1	μΑ
V <sub>CC</sub> Supply Current	Ivcc	$I/OVCC_{-} = V_{CC}, I/OVL_{-} = V_{L}, \overline{TS} = V_{L}$			35	μΑ
V Chutdown Mode Cupply		TS = GND, I/OVCC = unconnected		0.1	1	
V <sub>CC</sub> Shutdown Mode Supply Current	ISHDN_VCC	$\overline{TS} = V_{CC}$ , $V_L = GND$ , $I/OVCC = unconnected$		0.1	1	μΑ
V. Chutdown Mode Cupply		TS = GND		0.1	1	
V <sub>L</sub> Shutdown Mode Supply Current	I <sub>SHDN_VL</sub>	$\overline{TS} = V_L, V_{CC} = GND,$ I/OVL_ = unconnected		0.1	1	μΑ
I/OVCC_, I/OVL_, TS Leakage Current	I <sub>LEAK</sub>	$T_A = +25^{\circ}C, \overline{TS} = GND$		0.1	1	μΑ
TS Input Leakage Current	I <sub>LEAK_TS</sub>	$T_A = +25^{\circ}C$			1	μΑ
V <sub>L</sub> Shutdown Threshold	V <sub>TH_VL</sub>			0.3	0.85	V
V <sub>CC</sub> Shutdown Threshold	V <sub>TH_VCC</sub>			0.8	1.35	V
I/OVL_ Pullup Resistor	R <sub>VL_PU</sub>			10		kΩ
I/OVCC_ Pullup Resistor	R <sub>VCC_PU</sub>			10		kΩ

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{CC} = +1.65 \text{V to } +5.5 \text{V}, V_L = 0.9 \text{V to the lesser of } V_{CC} + 0.3 \text{V and } 5 \text{V}. T_A = T_J = -40 ^{\circ}\text{C}$  to  $+85 ^{\circ}\text{C}$ , unless otherwise noted. Typical values are at  $V_{CC} = +3.3 \text{V}, V_L = +1.8 \text{V}, T_A = +25 ^{\circ}\text{C}$ , unless otherwise noted.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
I/OVL_ to I/OVCC_ DC Resistance	R <sub>IOVL_IOVCC</sub>	Inferred from V <sub>OL</sub> measurements		5	10	Ω
I/OVL_ Input-Voltage High	V <sub>IHL</sub>		V <sub>L</sub> - 0.2			V
I/OVL_ Input-Voltage Low	V <sub>ILL</sub>				0.15	V
I/OVCC_ Input-Voltage High	V <sub>IHC</sub>		V <sub>CC</sub> - 0.4			V
I/OVCC_ Input-Voltage Low	V <sub>ILC</sub>				0.2	V
I/OVL_ Output-Voltage High	V <sub>OHL</sub>	I/OVL_ source current = 10µA	0.7 x V <sub>L</sub>			V
I/OVL_ Output-Voltage Low	V <sub>OLL</sub>	I/OVL_ sink current = 2mA, V <sub>I/OVCC</sub> ≤ 50mV			0.4	V
I/OVCC_ Output-Voltage High	V <sub>OHC</sub>	I/OVCC_ source current = 10µA	0.7 x V <sub>CC</sub>			V
I/OVCC_ Output Voltage Low	V <sub>OLC</sub>	I/OVCC_ sink current = 2mA, V <sub>I/OVL</sub> _ ≤ 150mV			0.4	V
TS Input-Voltage High Threshold	V <sub>IH</sub>		V <sub>L</sub> - 0.2			V
TS Input-Voltage Low Threshold	V <sub>IL</sub>	V <sub>L</sub> > 1.3V			0.2	V
Accelerator Pulse Duration		Inferred from timing measurements			30	ns
V <sub>L</sub> Output Accelerator Source		$V_L = 0.9V$	70			$\Omega$
Impedance		$V_L = 3.3V$		15		52
V <sub>CC</sub> Output Accelerator Source	$V_{CC} = 1.65V$			50		Ω
Impedance		V <sub>CC</sub> = 5.0V		10		_ \(\sigma\)
Thermal-Shutdown Threshold		20°C hysteresis		+150		°C
ESD PROTECTION						
I/OVCC_		Human Body Model, $C_{VCC} = 1\mu F$ , $C_{VL} = 0.1\mu F$		±6		kV
All Other Pins		Human Body Model		±2		kV

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **TIMING CHARACTERISTICS**

 $(V_{CC} = +1.65 \text{V to } +5.5 \text{V}, V_{L} = +0.9 \text{V to the lesser of } V_{CC} + 0.3 \text{V and } 5 \text{V}, \overline{TS} = V_{L}, R_{L} = 1 \text{M}\Omega, C_{VCC} = 1 \mu\text{F}, C_{VL} = 0.1 \mu\text{F}, C_{I/OVCC} = 15 \text{pF}, C_{I/OV$  $C_{I/OVL}$  = 15pF,  $T_A$  = -40°C to +85°C, unless otherwise noted. Typical values are  $V_{CC}$  = +3.3V,  $V_L$  = +1.8V, and  $T_A$  = +25°C.) (Note 4)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
LOVOC Bigg Time	+	Push-pull driving (Figure 1)	40		40		
I/OVCC_ Rise Time	tRVCC	Open-drain driving (Figure 2, Note 5)			100	ns	
LOVOC Foll Time	+	Push-pull driving (Figure 1)			40		
I/OVCC_ Fall Time	tFVCC	Open-drain driving (Figure 2, Note 5)			50	ns	
L/OVI Ding Time	+	Push-pull driving (Figure 3)			30	no	
I/OVL_ Rise Time	t <sub>RVL</sub>	Open-drain driving (Figure 4, Note 5)			105	ns	
L/OV/L Foll Times		Push-pull driving (Figure 3)			30		
I/OVL_ Fall Time	t <sub>FVL</sub>	Open-drain driving (Figure 4, Note 5)			30	ns	
Dramagation Dalou	I/O <sub>VL-VCC</sub>	Push-pull driving (Figure 1)			40	20	
Propagation Delay	I/O <sub>VL-VCC</sub>	Open-drain driving (Figure 2, Note 5)			150	ns	
Draw a gation Dalou	I/O <sub>VCC-VL</sub>	Push-pull driving (Figure 3)			30	- ns	
Propagation Delay	I/O <sub>VCC-VL</sub>	Open-drain driving (Figure 4, Note 5)			105		
Channel-to-Channel Skew		Input rise time/fall time < 6ns, push-pull driving			20		
Chamier-to-Chamier Skew	<sup>t</sup> skew	Input rise time/fall time < 6ns, open-drain driving			50	- ns	
Mayinguna Data Data	D D .	Push-pull operation			20	Mana	
Maximum Data Rate		Open-drain operation (Notes 5, 6)			6	Mbps	

- Note 2: All units are 100% production tested at  $T_A = +25$ °C. Specifications over operating temperature range are guaranteed by
- Note 3:  $V_L$  must be less than or equal to  $V_{CC}$  during normal operation. However,  $V_L$  can be greater than  $V_{CC}$  during startup and shutdown conditions.
- Note 4: All timing is 10% to 90% for rise time and 90% to 10% for fall time.
- **Note 5:** Not production tested; guaranteed by design.
- **Note 6:** Requires the external pullup resistor.

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

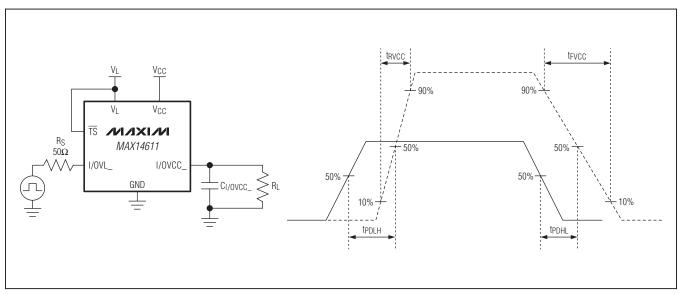


Figure 1. Push-Pull Driving I/OVL\_

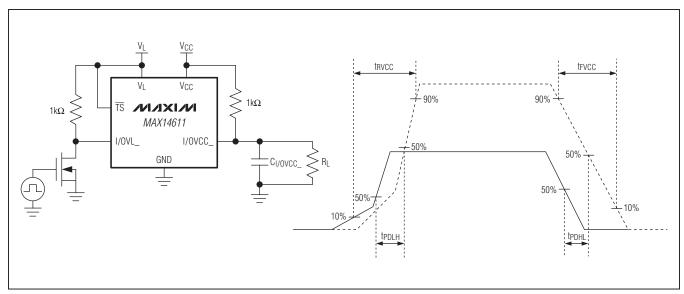


Figure 2. Open-Drain Driving I/OVL\_

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

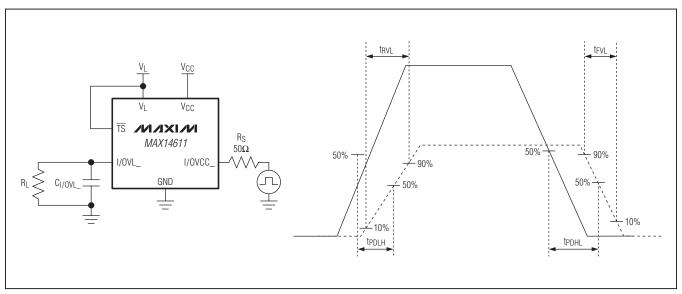


Figure 3. Push-Pull Driving I/OVCC\_

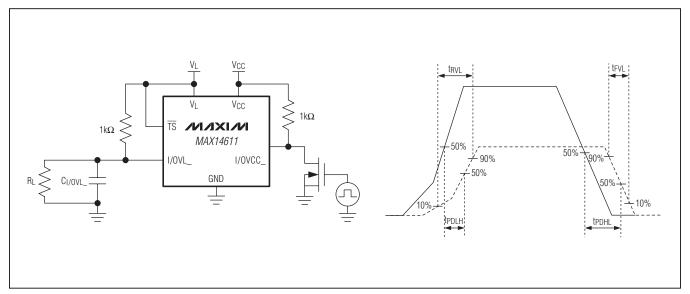
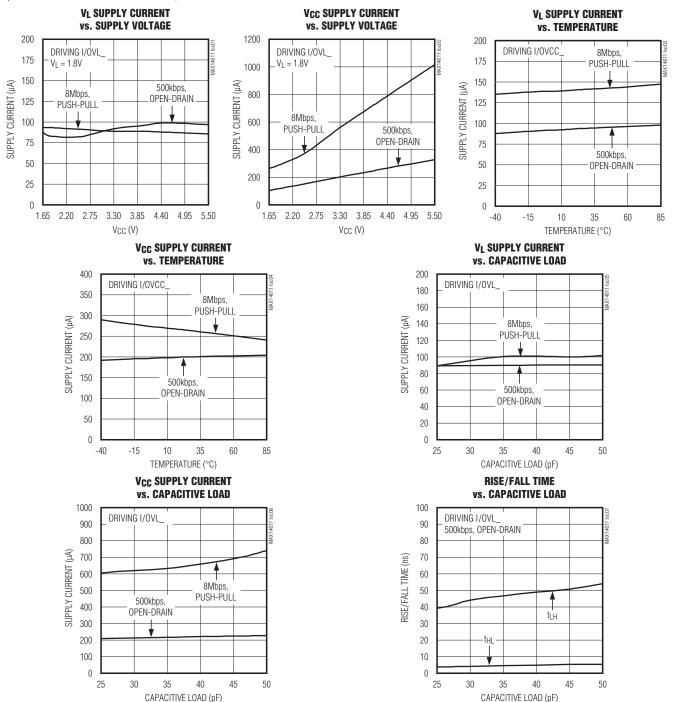


Figure 4. Open-Drain Driving I/OVCC\_

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **Typical Operating Characteristics**

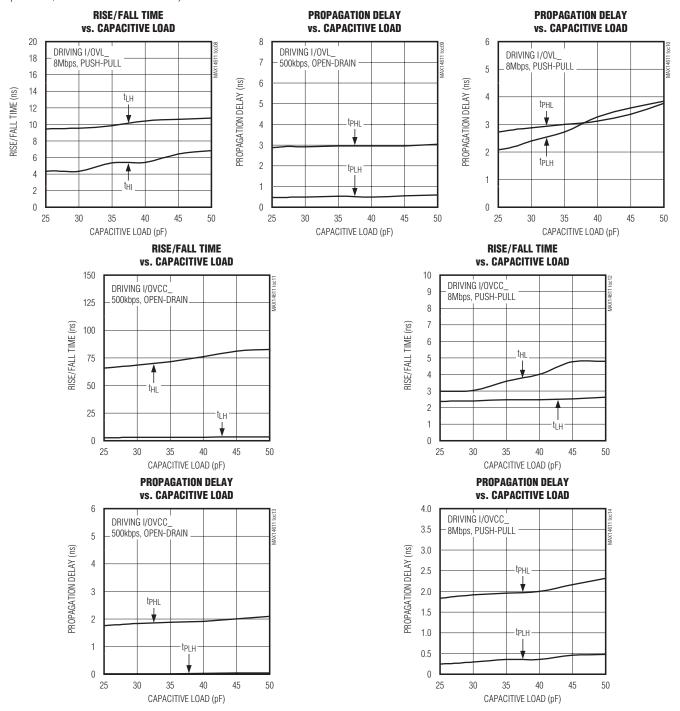
 $(V_{CC} = +3.3V, V_L = 1.8V, R_L = 1M\Omega, C_L = 15pF, T_A = +25^{\circ}C, data\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ open-drain\ operation\ open-drain\ operation\ open-drain\ open-dra$ operation, unless otherwise noted.)



# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **Typical Operating Characteristics (continued)**

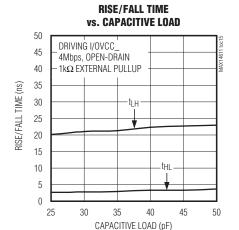
 $(V_{CC} = +3.3V, V_L = 1.8V, R_L = 1M\Omega, C_L = 15pF, T_A = +25^{\circ}C, data\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ open-drain\ operation\ open-drain\ operation\ open-drain\ open-dra$ operation, unless otherwise noted.)



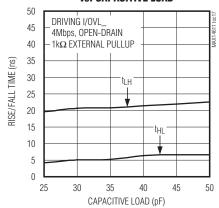
# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **Typical Operating Characteristics (continued)**

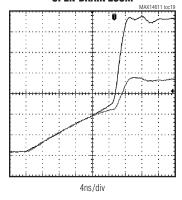
 $(V_{CC} = +3.3V, V_L = 1.8V, R_L = 1M\Omega, C_L = 15pF, T_A = +25^{\circ}C, data\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ push-pull\ rate = 500kbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ and\ 8Mbps\ in\ open-drain\ operation\ open-drain\ operation\ open-drain\ operation\ open-drain\ open-dra$ operation, unless otherwise noted.)



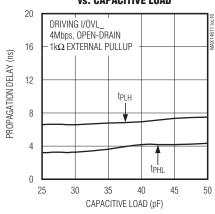
#### **RISE/FALL TIME** vs. CAPACITIVE LOAD



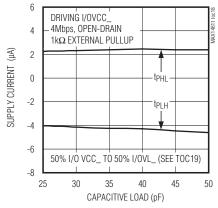
**LOW-TO-HIGH TRANSITION, OPEN-DRAIN ZOOM** 



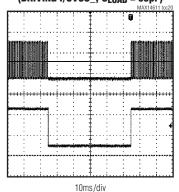
**PROPAGATION DELAY** vs. CAPACITIVE LOAD



**PROPAGATION DELAY** vs. CAPACITIVE LOAD

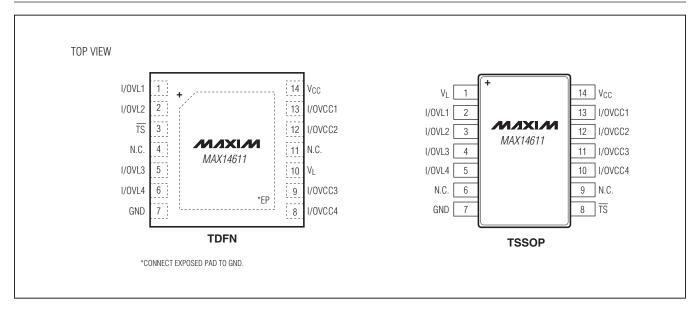


**ENTERING AND EXITING THREE-STATE MODE** (DRIVING I/OVCC\_, CLOAD = 50pF)



# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **Pin Configurations**

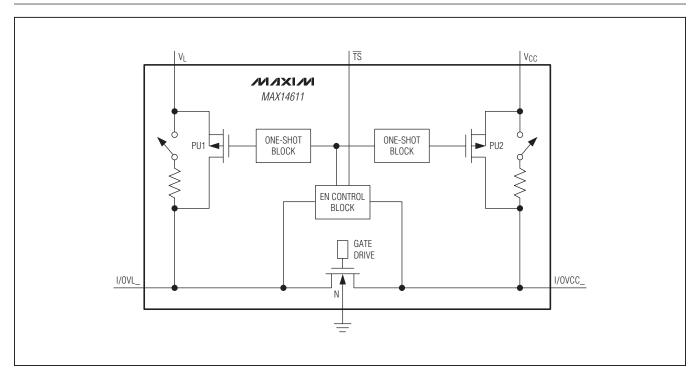


## **Pin Description**

PIN TDFN-EP TSSOP		NARAE	EUNCTION			
		NAME	FUNCTION			
1	2	I/OVL1	Input/Output 1. Reference to V <sub>L</sub> .			
2	3	I/OVL2	Input/Output 2. Reference to V <sub>L</sub> .			
3	8	TS	Three-State Select Input. Drive $\overline{\text{TS}}$ low to place the device in three-state output mode. I/OVCC_ and I/OVL_ are high impedance in three-state output mode.  Note: Logic referenced to V <sub>L</sub> (for logic thresholds, see the <i>Electrical Characteristics</i> table).			
4, 11	6,9	N.C.	No Connection. Not internally connected.			
5	4	I/OVL3	Input/Output 3. Reference to V <sub>L</sub> .			
6	5	I/OVL4	Input/Output 4. Reference to V <sub>L</sub> .			
7	7	GND	Ground			
8	10	I/OVCC4	Input/Output 4. Reference to V <sub>CC</sub> .			
9	11	I/OVCC3	Input/Output 3. Reference to V <sub>CC</sub> .			
10	1	VL	Logic Supply Voltage Input, $0.9V \le V_L \le min (5.0V, (V_{CC} + 0.3V))$ . Connect a $0.1\mu F$ ceramic capacitor as close as possible to the pin.			
12	12	I/OVCC2	Input/Output 2. Reference to V <sub>CC</sub> .			
13	13	I/OVCC1	Input/Output 1. Reference to V <sub>CC</sub> .			
14	14	V <sub>CC</sub>	Power Supply Input. The supply range is $1.65 \text{V} \le \text{V}_{\text{CC}} \le 5.5 \text{V}$ . Bypass $\text{V}_{\text{CC}}$ with a 1µF ceramic capacitor as close as possible to the pin to achieve higher ESD protection (±6kV HBM).			
		EP	Exposed Pad (TDFN Only). EP is internally connected to GND. Connect to a large ground plane to maximize thermal performance. Not intended as an electrical connection point.			

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

### **Functional Diagram**



#### **Detailed Description**

The MAX14611 ESD-protected level translator provides the level shifting necessary to allow data transfer in a multivoltage system. Externally applied voltages, V<sub>CC</sub> and V<sub>I</sub>, set the logic levels on either side of the device. A low-voltage logic signal present on the V<sub>I</sub> side of the device appears as a high-voltage logic signal on the Voc side of the device, and vice-versa.

The MAX14611 bidirectional level translator utilizes a transmission-gate based design (see the Functional Diagram) to allow data translation in either direction ( $V_L \leftrightarrow V_{CC}$ ) on any single data line. The device accepts  $V_{I}$  from +0.9V to +5.0V and  $V_{CC}$  from +1.65V to +5.5V, making it ideal for data transfer between lowvoltage ASICs/PLDs and higher voltage systems.

The device features a three-state output mode, thermal short-circuit protection, and ±6kV ESD protection on the V<sub>CC</sub> side for greater protection in applications that route signals externally.

#### **Level Translation**

For proper operation, ensure that  $+1.65V \le V_{CC} \le +5.5V$ ,  $0.9V \le V_L \le 5.0V$ , and  $V_L \le (V_{CC} + 0.3V)$ . It is permissible for V<sub>L</sub> to exceed (V<sub>CC</sub> + 0.3V) during power-up sequencing. During power-supply sequencing, when V<sub>CC</sub> is disconnected and  $V_{\rm I}$  is powered up, a current can be sourced without a latchup or any damage to the device. The maximum data rate of the MAX14611 depends heavily on load capacitance (see the Typical Operating Characteristics), output impedance of the driver, and the operational voltage (see the Timing Characteristics table).

#### **Speed-Up Circuitry**

The device features a one-shot generator that decreases the rise time of the output. When triggered following a rising edge, MOSFETs PU1 and PU2 turn on for a short time to pull up I/OVL\_ and I/OVCC\_ to their respective supplies (see the Functional Diagram). This greatly reduces the rise time and propagation delay for the low-to-high transition.

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

#### Rise-Time Accelerators (Figure 5)

The device has internal rise-time accelerators, allowing operation up to 20Mbps. The rise-time accelerators are present on both sides of the device and act to speed up the rise time of the input and output of the device, regardless of the direction of the data. The triggering mechanism for these accelerators is both level and edge sensitive. To prevent false triggering of the rise-time accelerators and to take full advantage of them, signal rise/fall times of less than 2ns/V are recommended for both sides of the device in open-drain driving. The recommendation applies only for fail time. Under less noisy conditions, longer signal fall times can be acceptable.

#### Three-State Output Mode (TS)

Drive TS low to place the device in three-state output mode. Connect TS to V<sub>I</sub> (logic-high) for normal operation. Activating the three-state output mode disconnects the internal  $10k\Omega$  pullup resistors on the I/OVCC and I/OVL\_ lines. This forces the I/O lines to a high-impedance state and decreases the supply current to less than 1µA. The high-impedance I/O lines in three-state output mode allow for use in a multidrop network. When in three-state output mode, keep the  $I/OVL_voltage$  below  $(V_L + 0.3V)$ , and keep the I/OVCC\_ voltage below ( $V_{CC} + 0.3V$ ).

#### **Thermal Short-Circuit Protection**

Thermal-overload detection protects the device from short-circuit fault conditions. In the event of a short-circuit fault and when the junction temperature (T<sub>.1</sub>) reaches +150°C (typ), a thermal sensor signals the three-state output mode logic to force the device into three-state output mode. When T<sub>J</sub> has cooled to +130°C (typ), normal operation resumes.

#### **High ESD Protection**

As with all Maxim devices, ESD-protection structures are incorporated on all pins to protect against electrostatic discharges encountered during handling and assembly. The I/OVCC lines have extra protection against static electricity. Maxim's engineers have developed state-ofthe-art structures to protect these pins against ESD of ±6kV without damage.

The ESD structures withstand high ESD in all states: normal operation, three-state output mode, and powered down. After an ESD event, the device keeps working without latchup, whereas competing products can latch and must be powered down to remove latchup. ESD protection can be tested in various ways. The I/OVCC\_ lines of this product family are characterized for protection.to ±6kV using the Human Body Model.

#### **ESD Test Conditions**

Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

#### **Applications Information**

#### **Power-Supply Decoupling**

Bypass V<sub>L</sub> to ground with a 0.1µF capacitor to reduce ripple and ensure correct data transmission. See the Typical Operating Circuit. To ensure full ±6kV ESD protection, bypass V<sub>CC</sub> to ground with a 1µF capacitor. Place all capacitors as close as possible to the powersupply pins (VCC and VI).

#### Push-Pull vs. Open-Drain Driving

The device can be driven in a push-pull configuration. The device includes internal  $10k\Omega$  resistors that pull up I/OVL\_ and I/OVCC\_ to their respective power supplies, allowing operation of the I/O lines with open-drain devices. See the Timing Characteristics table for maximum data rates when using open-drain drivers (Figure 1. Figure 2, Figure 3, Figure 4).

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

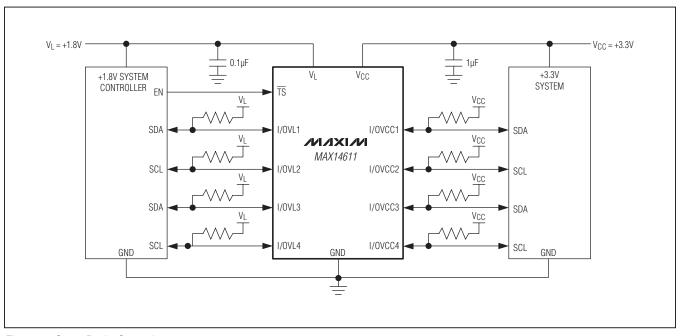
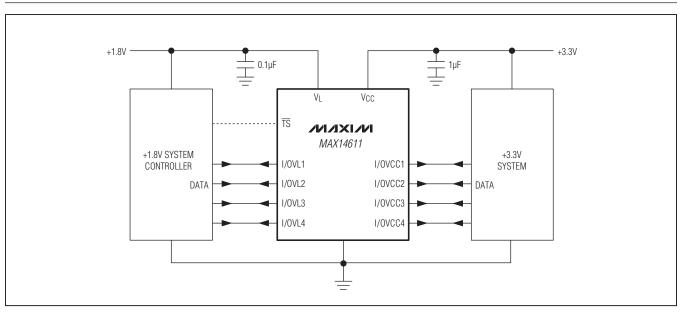


Figure 5. Open-Drain Operation

## **Applications Circuit**



**Package Information** 

# **Quad Bidirectional Low-Voltage Logic-Level Translator**

#### **Ordering Information**

PART	TEMP RANGE	PIN-PACKAGE
MAX14611ETD+	-40°C to +85°C	14 TDFN-EP*
MAX14611EUD+**	-40°C to +85°C	14 TSSOP

<sup>+</sup>Denotes a lead(Pb)-free/RoHS-compliant package.

### **Chip Information**

For the latest package outline information and land patterns (footprints), go to www.maxim-ic.com/packages. Note that a

"+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	OUTLINE NO.	LAND PATTERN NO.
14 TDFN-EP	T1433+2	21-0137	90-0063
14 TSSOP	U14+1	<u>21-0066</u>	<u>90-0113</u>

PROCESS: BICMOS

<sup>\*</sup>EP = Exposed pad.

<sup>\*\*</sup>Future product—contact factory for availability.

# Quad Bidirectional Low-Voltage Logic-Level Translator

## **Revision History**

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	4/12	Initial release	_

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time. The parametric values (min and max limits) shown in the Electrical Characteristics table are guaranteed. Other parametric values quoted in this data sheet are provided for guidance.